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Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics

Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)

AUTHOR INDEX

- Abbott, N.L., D10.7/G7.7
 Acosta, S., D5.26
 Adams, G.B., D3.8
 Albaugh, J., D5.18
 Alford, T.L., D9.6, D9.7, D9.11, D9.13
 Andleigh, V.K., D2.2
 Angyal, M., D3.8
 Arnaud, L., D2.4
 Ayral, A., D5.26
- Bae, B., D5.6
 Baklanov, M.R., D4.2, D5.14, D9.17
 Banger, K.K., D6.8
 Barnat, E., D10.5/G7.5
 Barr, D.L., D10.3/G7.3
 Barry, S., D9.12
 Baskaran, S., D4.5
 Batterman, B.W., D8.8, D10.3/G7.3
 Bender, H., D1.4
 Berger, T., D2.4
 Bergman, C., D10.10/G7.10
 Beyer, G.P., D 6.5, D9.17
 Beyne, E., D1.4
 Bhusari, D.M., D4.8
 Bierwag, A., D2.3
 Birnbaum, J., D4.5
 Blaschke, V.A., D2.3
 Boning, D.S., D11.8/E8.8
 Bonner, B.A., D11.6/E8.6, D11.8/E8.8
 Boyd, I.W., D5.17
 Braeckelmann, G., D1.2
 Bravman, J.C., D8.8, D10.3/G7.3
 Bremmer, J.N., D5.18
 Briggs, G.A.D., D1.7
 Brochard, C., D7.3
 Brongersma, S., D1.4
 Broomhall-Dillard, R.N., D9.12
 Brown, W.L., D8.8, D10.1/G7.1, D10.3/G7.3
- Cabral, Jr., C., D7.1, D7.5
 Cale, T.S., D9.16
- Caragianis-Broadbridge, C., D5.16
 Cargill III, G.S., D1.8, D8.6
 Case, C., D4.8
 Celestre, R.S., D8.8, D10.3/G7.3
 Chai, J.W., D9.18
 Chan, L., D8.4, D9.1
 Chang, C., D4.7
 Char, K., D3.6
 Chen, L., D9.11, D9.13
 Chen, Wei, D5.18
 Chen, Wei-Jung, D5.1
 Chen, Y-C., D10.5/G7.5
 Chery, Y., D2.2
 Cheung, D., D3.4
 Cho, Seon-Mee, D9.14
 Cho, Sung-Lae, D6.7
 Choi, I., D8.11
 Chopra, N., D3.4
 Chung, K., D5.18
 Claessen, R.U., D6.8
 Coenegrachts, B., D5.14
 Coffey, J.L., D5.10
 Conard, T., D9.17
 Cook, R.F., D5.4
 Cortez, R., D9.19
 Coyle, C., D4.5
- Dall, F., D5.12
 Dauskardt, R.H., D1.3
 David, J., D11.6/E8.6, D11.8/E8.8
 DeBear, D.S., D11.10/E8.10
 Dehate, E., D5.12
 Deis, T., D5.18
 Demkov, A.A., D3.8
 De Munari, I., D2.7
 Donaton, R.A., D5.14
 Duell, J., D5.11, D5.12
 Dull, T.L., D4.3
- Eisenbraun, E.T., D6.8
 Ekstrom, B., D1.2
 Elers, K., D6.4, D6.5

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Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)

- Evans, D.R., D3.3
 Evans-Lutterodt, K., D10.1/G7.1,
 D10.3/G7.3
 Everitt, D.L., D10.7/G7.7

 Fang, R., D9.19
 Fantini, F., D2.7
 Federspiel, X., D10.10/G7.10
 Felts, J.T., D5.3
 Filipiak, S., D1.2, D3.8
 Finch, V., D5.11, D5.12
 Fischer, A.H., D2.6, D8.9
 Fishkin, B., D11.6/E8.6
 Flinn, P., D10.3/G7.3
 Frieze, W.E., D4.3
 Fryxell, G.E., D4.5
 Fujimoto, H., D10.10/G7.10

 Gan, T., D11.8/E8.8
 Garretson, C., D11.6/E8.6
 Geer, R.E., D1.7
 Gidley, D.W., D4.3
 Gill, W.N., D5.25
 Goldberg, C., D1.2
 Gonella, R., D2.4
 Gordon, R.G., D9.12
 Grant, J.T., D9.20
 Gregory, R.B., D3.8
 Griffiths, D., D2.3
 Grill, A., D2.9
 Gross, M.E., D8.5, D10.1/G7.1,
 D10.3/G7.3
 Gu, H., D9.19
 Guettaz, L., D10.10/G7.10
 Guizard, C., D5.26
 Gutmann, R.J., D4.8

 Haberl, A., D5.25
 Han, J., D5.16
 Han, Q., D5.11
 Han, S., D5.6
 Hao, H., D7.5
 Harper, J.M., D7.5
 Hasegawa, S., D6.3
 Hasunuma, M., D2.5
 Haukka, S., D6.4, D6.5

 Hau-Riege, C.S., D2.2, D2.8
 Hau-Riege, S.P., D2.2, D8.7,
 D10.2/G7.2
 Havemann, R.H., D2.3
 Hayashi, T., D6.3
 Hein Lehman, A., D5.16
 Heiser, T., D7.3
 Herrick, M., D1.2
 Ho, P.S., D2.3
 Hommel, M., D2.6
 Homsí, W., D7.5
 Hong, J., D9.16
 Howard, K.E., D1.1
 Hsu, C., D5.23
 Hsu, S., D3.3
 Hu, C., D1.8
 Hu, X., D5.15
 Huan, C.H.A., 9.18
 Huang, T., D4.7
 Huang, T-F., D3.4
 Hwang, K.J., D8.6

 Iacoponi, J., D1.2
 Ignat, M., D10.10/G7.10
 Im, S., D6.7
 Inoki, C., D7.1
 Ito, S., D2.5
 Itoh, K., D11.2/E8.2
 Iwami, S., D11.3/E8.3

 Jackson, E., D1.2
 Jain, A., D5.25
 Jeng, U., D5.23
 Jin, C., D5.23
 Jin, Changming, D4.1, D4.5, D5.22
 Jin, H.J., D9.2
 Joo, Y., D8.11
 Justison, P.R., D2.3

 Kaloyeros, A.E., D6.8
 Kamezawa, M., D11.2/E8.2
 Kaneko, H., D2.5
 Kao, H., D1.8
 Katakabe, I., D11.2/E8.2
 Keller, R.R., D8.5, D10.3/G7.3
 Kihara, S., D11.2/E8.2

Cambridge University Press

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Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics

Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)

- Kim, H., D3.6
 Kim, Jung Joo, D8.1
 Kim, Junki, D8.1
 Kim, K., D6.7
 Kim, S., D6.7
 King, A.H., D10.8/G7.8
 Kinoshita, T., D9.2
 Kivilahti, J.K., D7.4
 Klemens, F.P., D4.8
 Kodera, M., D11.2/E8.2
 Koga, K., D9.2
 Kohl, P.A., D4.8
 Kolosov, O.V., D1.7
 Kornilov, A.M., D6.8
 Kottke, M., D3.8
 Kraemer, S., D8.5
 Kuan, T., D7.1
 Kwon, H., D8.1
- Lanckmans, F., D1.4
 Lanford, W., D5.25
 Laurila, T., D7.4
 Lavoie, C., D7.5
 Lecornec, C., D5.26
 Lee, B., D4.8
 Lee, B., D11.8/E8.8
 Lee, H., D5.23
 Lee, J-H., D3.4
 Lee, J.J., D1.2, D4.8
 Lee, Jin-Kyu, D3.6
 Lee, K., D2.3
 Lee, W., D8.1
 Leedy, K.D., D9.19, D9.20
 Lepage, M., D5.14
 Levert, J.A., D11.10/E8.10
 Li, X., D4.5
 Li, Xiang, D10.5/G7.5
 Li, Z., D9.14
 Liang, K.S., D5.23
 Lin, E.K., D4.1, D5.22
 Lin, H., D4.7
 Lin, M.Y., D5.8
 Lin, Mark, D4.7
 Lin, Mout-Lim, D4.7
 Lin, W., D5.1
 Liou, H., D5.11, D5.12
- Liu, J., D4.5
 Liu, R., D3.8
 Liu, Y., D5.18
 Lopata, E.S., D5.3
 Lormand, G., D2.4
 Lu, T., D5.23
 Lu, T-M., D10.5/G7.5
 Lu, Y-C., D3.4
 Luo, Z., D5.16
- Ma, J., D3.4
 MacDowell, A.A., D8.8, D10.3/G7.3
 Mack, A., D10.10/G7.10
 Maex, K., D1.4, D6.5, D9.17
 Malhotra, S.G., D7.5
 Mangat, R., D10.8/G7.8
 Marieb, T.N., D2.8, D8.6, D8.8, D10.3/G7.3, D10.10/G7.10
 Maris, H.J., D7.5
 Martin, J.I., D1.2
 Martin, S., D1.7
 Martin, Scott, D5.10
 Matsuhashi, H., D2.3
 Matsui, Y., D11.2/E8.2
 Matsuki, N., D5.14
 Mayer, J.W., D9.7
 McKeever, P., D11.8, E8.8
 Merchant, S., D10.1/G7.1
 Miecznikowski, J.R., D5.16
 Miller, W.J., D10.7/G7.7
 Mills, M.E., D1.1
 Miner, J., D4.8
 Miyashita, N., D11.2/E8.2, D11.3/E8.3
 Mizuno, S., D6.3
 Mogilnikov, K.P., D4.2
 Molarius, J., D7.4
 Moussavi, M., D5.26
 Moyer, E.S., D5.18
 Mridha, S., D9.1
 M'Saad, H., D9.14
 Mukherjee, S.P., D11.10/E8.10
 Murarka, S.P., D10.5/G7.5
- Nagahama, H., D6.3
 Nakagawa, Y., D6.3

Cambridge University Press

978-1-107-41315-3 - Materials Research Society Symposium Proceedings: Volume 612:
Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics
Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)

- Nakatake, Y., D9.2
 Naresh, P., D10.1/G7.1
 Nishioka, T., D11.3/E8.3
 Nucci, J.A., D8.5
 Numasawa, Y., D6.3

 Oehrlein, G., D7.1
 Ogawa, E.T., D2.3
 Oh, M., D10.1/G7.1
 O'Keefe, M.J., D9.19, D9.20
 O'Keefe, T.J., D9.19
 Osterday, R., D9.20
 Osterheld, T.H., D11.6/E8.6, D11.8/E8.8
 Owusu-Boahen, K., D10.8/G7.8

 Padmore, H.A., D8.8, D10.3/G7.3
 Pan, J.S., D9.18
 Pan, W., D3.3
 Park, H., D8.1
 Park, J., D8.1
 Park, K., D6.7
 Park, Y., D8.11
 Passemard, G., D5.26
 Patel, J.R., D8.8, D10.3/G7.3
 Patel, V.V., D2.9
 Pennetta, C., D2.7
 Phillibert, J., D10.10/G7.10
 Plawsky, J.L., D5.25
 Prasad, K., D8.4

 Qu, S., D5.8

 Rajan, K., D10.5/G7.5
 Ramamurthi, A., D2.3
 Reggiani, L., D2.7
 Rha, S., D8.1
 Rhee, H., D3.6
 Rhodes, L., D4.8
 Ro, H., D3.6
 Rogojevic, S., D5.25
 Rose, K., D7.1
 Rosenmayer, T., D5.8
 Rossnagel, S., D7.1
 Ruffin, R., D5.11

 Saha, C., D5.4, D5.18

 Saitoh, T., D11.2/E8.2
 Sakthivel, P., D5.11
 Sarkar, G., D5.15, D9.1
 Sato, M., D6.3
 Satta, A., D6.5
 Schaekers, M., D5.14
 Scorzoni, A., D2.7
 Seah, C., D9.1
 See, A.K., D5.15, D8.4
 Seppälä, A., D7.4
 Shaffer II, E.O., D1.1, D1.7
 Shekhawat, G.S., D1.7
 Shick, R., D4.8
 Shih, W.S., D9.19
 Shirakashi, M., D11.2/E8.2
 Shiratani, M., D9.2
 Sieloff, D., D1.2
 Siew, Y., D5.15, D9.1
 Sleenckx, E., D5.14
 Snodgrass, J.M., D1.3
 Snook, J.A., D9.19
 Sophie, G., D5.14
 Spaulding, M.J., D5.18
 Spolenak, R., D8.8, D10.3/G7.3
 Stecker, L.H., D3.3
 Struyf, H., D5.14
 Sun, J.N., D4.3
 Suni, I., D7.4
 Swaanen, M., D7.3

 Tamura, N., D8.8, D10.3/G7.3
 Taylor, K.J., D5.10
 Tee, K., D8.4
 Thompson, C.V., D2.2, D2.8, D8.7,
 D10.2/G7.2
 Toivola, Y., D5.4
 Toscano, P.J., D6.8
 Touet, I., D2.4
 Townsend III, P.H., D1.1
 Trefan, G., D2.7
 Troxel, D., D2.2
 Tsui, T.Y., D1.2
 Tsujimura, M., D11.2/E8.2
 Tuominen, M., D6.4
 Tweet, D.J., D3.3

Cambridge University Press

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Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics

Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)Uekusa, S., D11.3/E8.3
Usui, T., D2.5Valek, B.C., D8.8, D10.3/G7.3
Vanhaelemeersch, S., D5.14
Vantomme, A., D6.5
Varga, I., D1.4
Vellaikal, M., D9.14
Volkert, C.A., D8.5
von Glasow, A., D2.6Wagner, V.A., D9.12
Walther, D., D10.1/G7.1
Wang, F., D5.25
Wang, G., D7.1
Wang, P.-I., D10.5/G7.5
Wang, Y., D9.6, D9.7
Wang, Ying, D9.12
Watanabe, E., D6.3
Watanabe, Y., D9.2
Wayner, Jr., P.C., D5.25
Wedlake, M.D., D4.8
Wee, A.T.S., D9.18
Welch, J.T., D6.8
Werho, D., D3.8
Wetzel, J.T., D4.1, D5.22
Wickramanayaka, S., D6.3
Willecke, R., D3.4
Williford, R.E., D4.5Wilson, J.G., D9.20
Windover, D., D5.23
Wu, W., D4.1, D5.22Xu, P., D5.8
Xu, Y., D5.15Yamada, K., D11.2/E8.2
Yang, C., D5.1
Yang, D., D9.16
Yang, G.-R., D10.5/G7.5
Yang, H., D3.3
Yau, W.-F., D3.4
Yee, A.F., D4.3
Yieh, E., D3.4
Yoo, D., D3.6
Yoon, D.Y., D3.6
Young, L., D5.3Zeng, K., D7.4
Zeng, Y., D9.11, D9.13
Zerda, W., D5.10
Zhang, J.H., D9.18
Zhang, J.-Y., D5.17
Zhao, Y., D7.1
Zhu, W., D5.16
Zhu, X.D., D10.7/G7.7
Zitzelsberger, A.E., D2.6, D8.9
Zollner, S., D3.8

Cambridge University Press

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Index

[More information](#)

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Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics
Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel
Index

[More information](#)

SUBJECT INDEX

- adhesion, D1.1, D1.2, D1.4, D9.16
 - to copper, D9.14
- aerogels, D5.16
- Ag metallization, D9.7
- aging, D5.25
- air-gap(s), D4.7, D4.8
- ALCVD
 - technique, D6.4
 - TiN, D6.5
- aluminum, D8.6
- anneal, D9.17
- atomic force microscopy, D5.16
- AURORA, D5.14
- average pore size, D4.1

- barrier(s), D5.25, D9.20
 - film, D9.19
 - layer(s), D9.11, D9.13
- cage/network, D5.1
- chemical vapor deposition, D3.4
- cleaning, D11.2/E8.2
- CMP, D5.1, D11.2/E8.2
- concentration evolution, D1.8
- conformality, D6.5
- copper, D1.4, D3.9, D9.12, D9.17
 - contamination, D7.3
 - diffusion, D8.4
 - electroplating, D2.3
 - seed layer, D9.19
 - strain x-rays microdiffraction texture, D10.3/G7.3
- crystallographic texture, D8.1
- Cu, D6.7, D11.2/E8.2
 - barrier, D6.4
 - CVD, D9.16
 - electromigration, D2.3
 - interconnects, D2.3, D4.8
 - metallization, D9.18
- curing, D5.1, D5.12
- CVD, D3.4, D6.7
 - ultrathin seed layer electroplating, D6.8

- damascene, D3.9, D5.14
 - copper, D2.4
- damping, D7.5
- debonding, D1.3
- dielectric, D1.3, D4.5
 - constant, D5.6
 - thin film D4.3

- diffusion barrier, D7.3, D7.4, D9.12, D9.18
 - formation, D9.6
- dimethylaluminum hydride, D8.1
- dry stripping, D5.11
- dual damascene, D6.4

- electrical resistivity, D7.1
- electrochemical deposition, D9.19
- electromigration, D1.8, D2.2, D2.3, D2.4, D2.7, D2.8, D8.6, D8.7, D8.8, D10.2/G7.2
- electroplated copper, D10.1/G7.1
- ellipsometry, D4.2
- excimer lamp, D5.17

- failure models, D2.7
- FaSEPP, D8.11
- fatigue, D1.3
- fluorine doped silicon dioxide, D5.10
- fluorocarbon, D5.6
- flux divergence, D8.11
- focused ion beam, D10.1/G7.1
- fox, D5.18
- fracture toughness, D5.25
- fsg, D1.2
- full-chip, D2.2

- gate electrodes, D9.12
- geometric transitions, D2.8
- grain
 - growth, D9.1
 - size, D9.2
 - effect, D7.1

- H₂/N₂, D5.12
- HOLZ lines, D8.5
- HSQ, D5.1, D5.11, D5.12, D5.15, D9.11, D9.13
- hybrid templating, D5.15
- hydrogen
 - plasma, D9.17
 - silsesquioxane, D5.11, D5.12, D5.18

- integration, D5.3, D5.14
- interlayer dielectrics, D2.5
- interconnect(s), D1.1, D4.2, D4.5, D8.8, D9.2
- interconnection structure, D5.4
- interface, D7.5
 - adhesion, D1.3
- interfacial energy, D9.7
- interlevel dielectrics, D5.16

Cambridge University Press

978-1-107-41315-3 - Materials Research Society Symposium Proceedings: Volume 612:
Materials, Technology and Reliability for Advanced Interconnects and Low-k Dielectrics
Editors: G. S. Oehrlein, K. Maex, Y. -C. Joo, S. Ogawa and J. T. Wetzel

Index

[More information](#)

- intermetal dielectric, D4.5
- intra-metal air-gap, D4.7
- ion beam, D6.7
- I-PVD TiN, D6.5
- Korhonen model, D10.2/G7.2
- leakage current density, D9.14
- lifetime, D2.6, D8.9
- low
 - dielectric, D5.11
 - constant, D5.17
 - insulators, D5.16
 - material, D4.8
 - k, D1.1, D1.4, D2.5, D3.4, D3.6, D5.14, D9.14
 - dielectric(s), D1.7, D3.9, D4.2, D5.8, D5.22, D5.26, D9.11, D10.2/G7.2
 - materials, D5.23, D9.13
- mechanical
 - properties, D1.1, D8.8
 - strength, D5.8
- metal interdiffusion, D4.3
- metallization, D8.9
- metrology, D1.7
- microstructure, D2.8, D8.5
- Monte Carlo simulations, D7.1
- morphology, D6.5
- multilevel
 - interconnect, D2.5
 - metal interconnect, D4.7
- nanocomposites, D5.8
- nanindentation, D5.4
- nanoporous, D5.15
- nitrides, D9.11
- normal pulse plating, D9.1
- nucleation, D9.16
- off-period, D9.1
- organic solution, D9.19
- oscillation, D7.5
- percolation, D2.7
- pH, D11.3/E8.3
- phase
 - diagrams, D7.4
 - morphology, D5.8
- photo-assisted sol-gel processing, D5.17
- photoresist, D5.11
- PMSSQ, D3.6
- polymer, D1.3
- poly(methylsilsequioxane), D3.6
- pore
 - connectivity, D4.1
 - size, D5.22
 - distribution, D4.2, D4.3
- porosity, D4.1, D4.2, D5.22, D5.25, D5.26
- porous, D4.5
 - SiO₂ film, D5.17
 - thin film, D4.3
- PTFE, D5.8
- PVD, D9.20
- Raman spectroscopy, D5.10
- RCAD, D2.2, D8.7
- recrystallization, D10.1/G7.1
- reliability, D1.2, D2.6, D2.7, D8.5, D8.9
- reservoir, D8.7
- resistivity, D6.5, D9.6
- ring defects, D5.10
- sacrificial polymer, D4.8
- SAXS, D5.23
- shear test, D1.4
- silica thin layer, D5.26
- silicon devices, D8.4
- silsequioxane, D5.4
- SiOC, D3.4, D5.14
- size and surface effects, D7.1
- sol-gel, D5.26
- step coverage, D8.1
- stress(-), D8.6
 - evolution, D1.8
 - void, D2.6
- surface, D9.17
 - morphology, D9.16
 - reaction probability, D9.2
 - roughness, D9.2
- surfactant(-), D11.3/E8.3
 - templated, D4.5
- synchrotron, D8.8
- Ta, D9.18
- TaN, D6.7
- tantalum, D1.2
- texture, D2.4, D10.1/G7.1
- thermal, D8.6
 - stability, D5.3, D5.6, D8.4, D9.6
- thermodynamics, D7.4
- thin film(s), D5.12, D8.6, D8.8
- TID, D7.3
- toughness, D1.1
- tungsten
 - nitride, D9.12, D9.20
 - oxide, D9.12
- two-stage treatment, D5.15

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Index
[More information](#)

ULSI integration, D2.3	water vapor, D9.16
ultrasonic force microscopy, D1.7	
via	xerogel(s), D5.16, D5.23
electromigration reliability, D2.5	XPS, D9.20, D11.2/E8.2
filling, D8.1	x-ray microbeam, D1.8
resistance, D8.1	
viscosity, D11.3/E8.3	Young's modulus, D2.5
VLK, D5.3	